

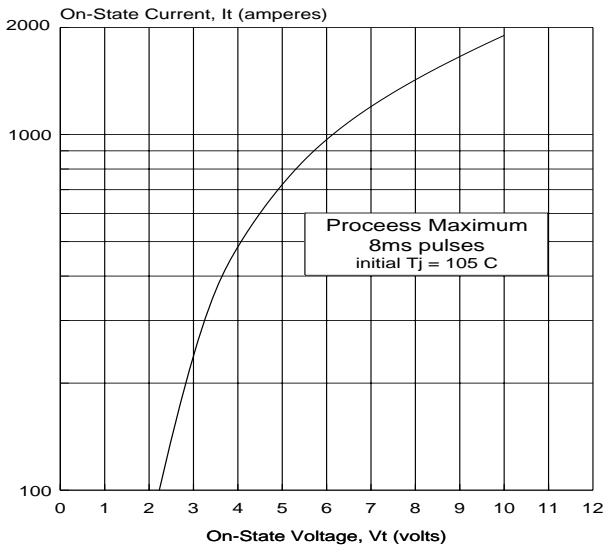
SDT123

53mm / 9kV THYRISTOR

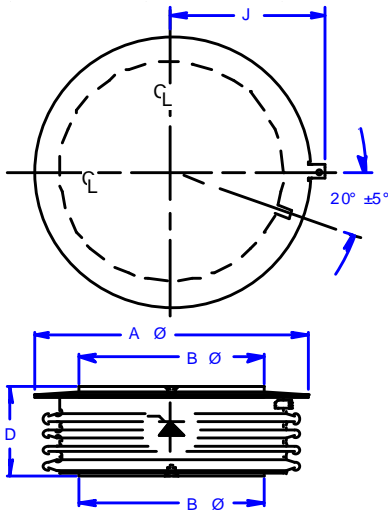
Type SDT123 thyristor is suitable for phase control applications such as HVDC valves, static VAR compensators and synchronous motor drives.

The silicon junction is manufactured by the proven multi-diffusion process and is supplied in an industry standard disc-type package, ready to mount to forced or naturally cooled heat dissipators using commercially available mechanical clamping hardware.

ON-STATE CHARACTERISTIC



MECHANICAL OUTLINE



A Φ = 2.96 in (75.2 mm)
B Φ = 1.90 in (48.3 mm)
D = 1.07 in (27.2 mm)

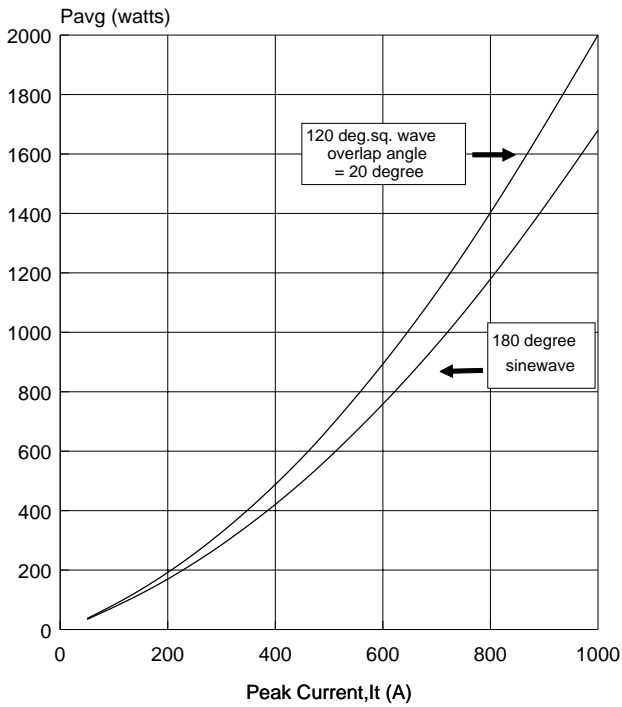
PRINCIPAL RATINGS AND CHARACTERISTICS

| | | | | |
|--|------------------------|--|--|----------|
| Repetitive peak off-state & reverse volts | V_{DRM} V_{RRM} | $T_J=0$ to 110°C | up to 9000 | V |
| Repetitive working crest voltage | V_{DWM} V_{RWM} | $T_J=0$ to 110°C | $0.8V_{DRM}$ $0.8V_{RRM}$ | V |
| off-state & reverse leakage current | I_{DWM} I_{RWM} | $T_J=0$ to 110°C | 100 100 | ma |
| Average on-state current | $I_{T(AV)}$ | $T_{case} = 70^\circ\text{C}$ | 300 | A |
| Peak half-cycle non-rep surge current | I_{TSM} | 60 Hz 50 Hz | 2650 2350 | A |
| On-state voltage | V_{TM} | $I_T=500\text{A}$ $t_p=8\text{ms}$ $T_J=105^\circ\text{C}$ | 4.0 | V |
| Critical rate of rise of on-state current | di/dt_{rep} | $T_J=110^\circ\text{C}$ 60 Hz | 40 | A/us |
| allowable snubber discharge | $V_d = .67V_{DRM}$ | | 50 | A |
| Critical rate of rise of off-state voltage | dv/dt | $T_J=110^\circ\text{C}$ $V_{DCRIT} = 60\% V_{DRM}$ | 2000 | V/us |
| Recovery current | I_{RM} | $T_J=110^\circ\text{C}$ 2A/us 5A/us | 85 135 | A |
| | | minimum snub factor $S = 0.3$ | | |
| Turn-on delay | t_a | $V_d = .5V_{DRM}$ | 8 | us |
| Turn-off time | T_{off} | 5A/us, -100V 20V/us to 2000V | 900 | us |
| Thermal resistance | R_{thJC} | | .025 | c/w |
| Externally applied clamping force | F | | 5500 24.5 | lb kN |
| Gate Drive: | | | 50V / 10 ohm / 0.5us risetime 20us pulse duration | |

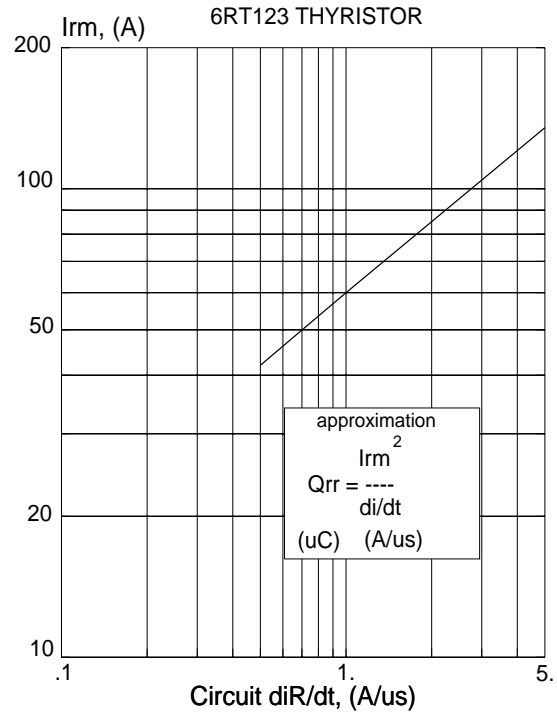
REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE

| MODEL | V_{DRM} (volts) | V_{RRM} (volts) |
|----------|----------------------|----------------------|
| SDT123RT | 9000 | 9000 |
| SDT123RK | 8500 | 8500 |
| SDT123PT | 7000 | 8000 |
| SDT123PK | 7500 | 7500 |

FULL CYCLE AVERAGE POWER LOSS
versus
PEAK CURRENT at 50/60 Hz
(plasma spreading and conduction loss)



MAXIMUM PEAK RECOVERY CURRENT
T_J = 110 C



95c:T123 5/6/95

Full Cycle Power Loss (watts)
50/60 Hz, T_J=110°C

| I _T (peak) (A) | Half-sine | | 3 Phase 120° |
|------------------------------|-----------|------|-----------------|
| | 180° | 120° | |
| 50 | 34 | 37 | |
| 100 | 75 | 82 | |
| 150 | 119 | 133 | |
| 200 | 169 | 191 | |
| 250 | 224 | 255 | |
| 300 | 284 | 326 | |
| 350 | 350 | 403 | |
| 400 | 420 | 487 | |
| 450 | 496 | 577 | |
| 500 | 577 | 675 | |
| 600 | 755 | 889 | |
| 700 | 954 | 1130 | |
| 800 | 1175 | 1397 | |
| 900 | 1417 | 1692 | |
| 1000 | 1680 | 2014 | |

GATE SUPPLY REQUIREMENTS

| | |
|-----------------------|-------|
| Open circuit voltage | 40 V |
| Short circuit current | 4 A |
| - rise time | 0.5μs |
| Pulse duration (min) | 20 μs |